

Kohei Fujiwara

List of Publications by Year in descending order

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64
papers

1,228
citations

430874
18
h-index

395702
33
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64
all docs

64
docs citations

64
times ranked

1928
citing authors

#	ARTICLE	IF	CITATIONS
1	Resistance Switching and Formation of a Conductive Bridge in Metal/Binary Oxide/Metal Structure for Memory Devices. Japanese Journal of Applied Physics, 2008, 47, 6266.	1.5	146
2	Accumulation and Depletion Layer Thicknesses in Organic Field Effect Transistors. Japanese Journal of Applied Physics, 2003, 42, L1408-L1410.	1.5	105
3	5d iridium oxide as a material for spin-current detection. Nature Communications, 2013, 4, 2893.	12.8	104
4	Inhomogeneous chemical states in resistance-switching devices with a planar-type Pt/CuO/Pt structure. Applied Physics Letters, 2009, 95, .	3.3	94
5	Giant magneto-optical responses in magnetic Weyl semimetal Co ₃ Sn ₂ S ₂ . Nature Communications, 2020, 11, 4619.	12.8	92
6	Highly conductive PdCoO ₂ ultrathin films for transparent electrodes. APL Materials, 2018, 6, .	5.1	45
7	Anomalous State Sandwiched between Fermi Liquid and Charge Ordered Mott-insulating Phases of $Ti_{4-x}O_x$. Physical Review Letters, 2010, 104, 106401.	7.8	29
8	Enhanced electron mobility at the two-dimensional metallic surface of BaSnO ₃ electric-double-layer transistor at low temperatures. Applied Physics Letters, 2017, 110, .	3.3	26
9	Ferromagnetic Co ₃ Sn ₂ S ₂ thin films fabricated by co-sputtering. Japanese Journal of Applied Physics, 2019, 58, 050912.	1.5	26
10	Fe-Sn nanocrystalline films for flexible magnetic sensors with high thermal stability. Scientific Reports, 2019, 9, 3282.	3.3	26
11	Critical thickness for the emergence of Weyl features in Co ₃ Sn ₂ S ₂ thin films. Communications Materials, 2021, 2, .	6.9	23
12	First-principles investigation of magnetic and transport properties in hole-doped shandite compounds $Co_{3-x}S_{2+x}$. Physical Review B, 2021, 103, .	3.6	21
13	Tuning metal-insulator transition by one dimensional alignment of giant electronic domains in artificially size-controlled epitaxial VO ₂ wires. Applied Physics Letters, 2012, 101, 263111.	3.3	20
14	Nanowall-Shaped MgO Substrate with Flat (100) Sidesurface: A New Route to Three-Dimensional Functional Oxide Nanostructured Electronics. Japanese Journal of Applied Physics, 2013, 52, 015001.	1.5	20
15	Thin-film stabilization of LiNbO ₃ -type ZnSnO ₃ and MgSnO ₃ by molecular-beam epitaxy. APL Materials, 2019, 7, .	5.1	20
16	Anomalous Hall effect at the spontaneously electron-doped polar surface of $PdCo_{3-x}O_x$. Physical Review Research, 2020, 2, .	3.6	20
17	Identification of Giant Mott Phase Transition of Single Electric Nanodomain in Manganite Nanowall Wire. Nano Letters, 2015, 15, 4322-4328.	9.1	19
18	Dual field effects in electrolyte-gated spinel ferrite: electrostatic carrier doping and redox reactions. Scientific Reports, 2014, 4, 5818.	3.3	18

#	ARTICLE	IF	CITATIONS
19	Controlled fabrication of artificial ferromagnetic $(\text{Fe},\text{Mn})_3\text{O}_4$ nanowall-wires by a three-dimensional nanotemplate pulsed laser deposition method. <i>Nanotechnology</i> , 2012, 23, 485308.	2.6	16
20	High field-effect mobility at the $(\text{Sr},\text{Ba})\text{SnO}_3/\text{BaSnO}_3$ interface. <i>AIP Advances</i> , 2016, 6, 085014.	1.3	16
21	Spatial Redistribution of Oxygen Ions in Oxide Resistance Switching Device after Forming Process. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 060215.	1.5	15
22	Electric field-induced transport modulation in VO_2 FETs with high- <i>k</i> oxide/organic polyethylene-C hybrid gate dielectric. <i>Applied Physics Letters</i> , 2016, 108, 053503.	3.3	15
23	Magnetic-field-induced topological phase transition in Fe-doped $\text{Fe}_{\text{Fe}}(\text{Fe},\text{Zn})_3\text{O}_4$ heterostructures. <i>Physical Review Materials</i> , 2020, 4,	2.4	15
24	Electric-field breakdown of the insulating charge-ordered state in LuFe_2O_4 thin films. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 155108.	2.8	14
25	Nonvolatile Transport States in Ferrite Thin Films Induced by Field-Effect Involving Redox Processes. <i>Advanced Materials Interfaces</i> , 2014, 1, 1300108.	3.7	14
26	Fabrication of three-dimensional epitaxial $(\text{Fe},\text{Zn})_3\text{O}_4$ nanowall wire structures and their transport properties. <i>Applied Physics Express</i> , 2014, 7, 045201.	2.4	14
27	Formation of distorted rutile-type NbO_2 , MoO_2 , and WO_2 films by reactive sputtering. <i>Journal of Applied Physics</i> , 2019, 125,	2.5	14
28	V-V dimerization effects on bulk-sensitive hard x-ray photoemission spectra for Magneli phase vanadium oxides. <i>Physical Review B</i> , 2010, 81, .	3.2	13
29	Observation of rebirth of metallic paths during resistance switching of metal nanowire. <i>Applied Physics Letters</i> , 2013, 103, 193114.	3.3	13
30	Fermi-level tuning of the Dirac surface state in $(\text{Bi}_{1-x}\text{Sb}_x)_2\text{Se}_3$ thin films. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 085501.	1.8	13
31	Enhancement of superconducting transition temperature in FeSe electric-double-layer transistor with multivalent ionic liquids. <i>Physical Review Materials</i> , 2018, 2, .	2.4	13
32	Three dimensional nano-seeding assembly of ferromagnetic Fe/LaSrFeO ₄ nano-hetero dot array. <i>Journal of Applied Physics</i> , 2012, 112, 024320.	2.5	12
33	Fabrication of tetragonal $\text{FeSe}-\text{FeS}$ alloy films with high sulfur contents by alternate deposition. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 100308.	1.5	11
34	3D-Architected and Integrated Metal Oxide Nanostructures and Beyond Produced by Three-Dimensional Nanotemplate Pulsed Laser Deposition. <i>E-Journal of Surface Science and Nanotechnology</i> , 2015, 13, 279-283.	0.4	10
35	3D-Architected and Integrated Metal Oxide Nanostructures and Beyond Produced by Three-Dimensional Nanotemplate Pulsed Laser Deposition. <i>E-Journal of Surface Science and Nanotechnology</i> , 2015, 13, 279-283.	3.2	10
36	Emergence of spin-orbit coupled ferromagnetic surface state derived from Zak phase in a nonmagnetic insulator FeSi. <i>Science Advances</i> , 2021, 7, eabj0498.	10.3	10

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37	Pulsed-laser deposition of InSe thin films for the detection of thickness-dependent bandgap modification. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	9
38	Doping-induced enhancement of anomalous Hall coefficient in Fe-Sn nanocrystalline films for highly sensitive Hall sensors. <i>APL Materials</i> , 2019, 7, .	5.1	9
39	Electrical detection of the antiferromagnetic transition in MnTiO ₃ ultrathin films by spin Hall magnetoresistance. <i>Journal of Applied Physics</i> , 2020, 127, 103903.	2.5	8
40	Three-dimensional sensing of the magnetic-field vector by a compact planar-type Hall device. <i>Communications Materials</i> , 2021, 2, .	6.9	8
41	Electrode-Geometry Control of the Formation of a Conductive Bridge in Oxide Resistance Switching Devices. <i>Applied Physics Express</i> , 2009, 2, 081401.	2.4	7
42	Effect of the depletion region in topological insulator heterostructures for ambipolar field-effect transistors. <i>Physical Review B</i> , 2018, 98, .	3.2	7
43	Low-frequency noise measurements on Fe-Sn Hall sensors. <i>Applied Physics Express</i> , 2019, 12, 123001.	2.4	7
44	Robust perpendicular magnetic anisotropy of $\text{Co}_{2.4}S_{2.7}$ phase in sulfur deficient sputtered thin films. <i>Physical Review Materials</i> , 2021, 5, .	2.4	7
45	Two-dimensionality of metallic surface conduction in Co ₃ Sn ₂ S ₂ thin films. <i>Communications Physics</i> , 2021, 4, .	5.3	7
46	Unstrained Epitaxial Zn-Substituted Fe ₃ O ₄ Films for Ferromagnetic Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 068002.	1.5	6
47	Estimation of dc transport dynamics in strongly correlated (La,Pr,Ca)MnO ₃ film using an insulator-metal composite model for terahertz conductivity. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	6
48	Artificial three dimensional oxide nanostructures for high performance correlated oxide nanoelectronics. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 05FA10.	1.5	6
49	Discrimination between gate-induced electrostatic and electrochemical characteristics in insulator-to-metal transition of manganite thin films. <i>Applied Physics Express</i> , 2015, 8, 073201.	2.4	6
50	High-mobility field-effect transistor based on crystalline ZnSnO ₃ thin films. <i>AIP Advances</i> , 2018, 8, .	1.3	6
51	In-Plane Oblique Pulsed-Laser Deposition and Its Application to the Fabrication of Metal Oxide Nanoconstrictions. <i>Applied Physics Express</i> , 2013, 6, 035201.	2.4	5
52	Impact of parylene-C thickness on performance of KTaO ₃ field-effect transistors with high-k oxide/parylene-C hybrid gate dielectric. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	5
53	Stabilization of a honeycomb lattice of IrO ₆ octahedra by formation of ilmenite-type superlattices in MnTiO ₃ . <i>Communications Materials</i> , 2020, 1, .	6.9	5
54	Insulator-to-Metal Transition of Cr ₂ O ₃ Thin Films via Isovalent Ru ³⁺ Substitution. <i>Chemistry of Materials</i> , 2020, 32, 5272-5279.	6.7	5

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55	Growth control of corundum-derivative MnSnO ₃ thin films by pulsed-laser deposition. AIP Advances, 2019, 9, 035210.	1.3	4
56	Tuning scalar spin chirality in ultrathin films of the kagome-lattice ferromagnet Fe ₃ Sn. Communications Materials, 2021, 2, .	6.9	4
57	Formation of ilmenite-type single-crystalline MgTiO ₃ thin films by pulsed-laser deposition. AIP Advances, 2021, 11, .	1.3	4
58	Improving resistance change with temperature and thermal stability in Fe ₃ O ₄ films for high-temperature resistors. Applied Physics Express, 2019, 12, 011003.	2.4	3
59	Electrical switching to probe complex phases in a frustrated manganite. Solid State Communications, 2014, 187, 64-67.	1.9	1
60	Improvement of the detectivity in an Fe-Sn magnetic-field sensor with a large current injection. Japanese Journal of Applied Physics, 2022, 61, SCI069.	1.5	1
61	Electrostatic carrier doping of charge-ordered YbFe ₂ O ₄ thin films using ionic liquids. Applied Physics Express, 2021, 14, 083001.	2.4	0
62	Oxide Field-Effect Transistor with Polymer-Based Gate Insulator. IEEJ Transactions on Electronics, Information and Systems, 2019, 139, 207-210.	0.2	0
63	A large unidirectional magnetoresistance in Fe-Sn heterostructure devices. Japanese Journal of Applied Physics, 0, .	1.5	0
64	Co_{2}FeSn ordering of Co ₂ FeSn thin films promoted by high-temperature annealing. AIP Advances, 2022, 12, 065030.	1.3	0